



SHEET 1 OF 4

Form PTO 1449
(Modified)U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY DOCKET NO.
210136US99SERIAL NO.
09/901,109

LIST OF REFERENCES CITED BY APPLICANT

APPLICANT

Ravindranath DROOPAD, et al.

FILING DATE
July 10, 2001GROUP
2815

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
WMB	XN	6,233,435 B1	05/15/01	WONG			
	XO	4,723,321	02/02/88	SALEH			
	XP	6,181,920 B1	01/30/01	DENT ET AL			
	XQ	6,415,140 B1	07/02/02	BENJAMIN ET AL			
	XR	5,760,740	06/02/98	BLODGETT			
	XS	5,238,877	08/24/93	RUSSELL			
	XT	4,876,218	10/24/89	PESSA ET AL			
	XU	6,232,242 B1	05/15/01	HATA ET AL			
	XV	4,378,259	03/29/83	HASEGAWA ET AL			
	XW	6,278,541 B1	08/21/01	BAKER			
	XY	4,298,247	11/03/81	MICHELET ET AL			
	XZ	4,174,504	11/13/79	CHENAUSSKY ET AL			
	YA	3,758,199	09/11/73	THAXTER			
	YB	6,362,558 B1	03/26/02	FUKUI			
	YC	6,140,746	10/31/00	MIYASHITA ET AL			
	YD	2002/0076878 A1	06/20/02	WASA ET AL			
	YE	6,419,849 B1	07/16/02	QIU ET AL			
	YF	2002/0179000 A1	12/05/02	LEE ET AL			
	YG	6,341,851	01/29/02	TAKAYAMA ET AL			
	YH	2001/0055820 A1	12/27/01	SAKURAI ET AL			
YI	6,204,525 B1	03/20/01	SAKURAI ET AL				
YJ	5,985,404	11/16/99	YANO ET AL				
YK	6,538,359 B1	03/25/03	HIRAKU ET AL				
YL	6,498,358 B1	12/24/02	LACH ET AL				
YM	5,387,811	02/07/95	SAIGOH				
YN	5,523,602	06/04/96	HORIUCHI ET AL				
YO	5,362,998	11/08/94	IWAMURA ET AL				
YP	5,188,976	02/23/93	KUME ET AL				

Examiner

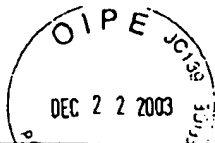
Date Considered

2/27/04

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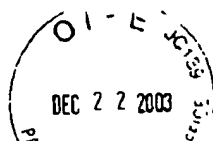
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U.S. PATENT DOCUMENTS							
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bwb	YQ	6,501,121 B1	12/31/02	YU ET AL			
	YR	5,919,515	07/06/99	YANO ET AL			
	YS	5,238,877	08/24/93	RUSSELL			
	YT	5,540,785	07/30/96	DENNARD ET AL			
	YU	5,997,638	12/07/99	COPEL ET AL			
	YV	6,291,866	09/18/01	WALLACE			
	YW	5,365,477	11/15/94	COOPER, JR ET AL			
	YX	5,548,141	08/20/96	MORRIS ET AL			
	YY	2002/0021855	02/21/02	KIM			
	YZ	6,110,840	08/29/00	YU			
	ZA	5,667,586	09/16/97	EK ET AL			
	ZB	5,313,058	05/17/94	FRIEDERICH ET AL			
	ZC	5,315,128	05/24/94	HUNT ET AL			
	ZD	5,919,522	07/06/99	BAUM ET AL			
	ZE	4,843,609	06/27/89	OHYA ET AL			
	ZF	4,626,878	12/02/86	KUWANO ET AL			
	ZG	4,525,871	06/25/85	FOYT ET AL			
	ZH	3,818,451	06/18/74	COLEMAN			
	ZI	6,059,895	05/09/00	CHU ET AL			
	ZJ	4,447,116	05/08/84	KING ET AL			
	ZK	6,022,671	02/08/00	BINKLEY ET AL			
	ZL	5,754,714	05/19/98	SUZUKI ET AL			
	ZM	6,524,651 B2	02/25/03	GAN ET AL			
	ZN	6,355,945 B1	03/12/03	KADOTA ET AL			
	ZO	5,642,371	06/24/97	TOHYAMA ET AL			
	ZP	6,445,724 B2	09/03/02	ABELES			
	ZQ	5,753,934	05/19/98	YANO ET AL			
	ZR	6,326,667 B1	12/04/01	SUGIYAMA ET AL			
ZS	6,051,874	04/18/00	MASUDA				
ZT	5,166,761	11/24/92	OLSON ET AL				
ZU	5,574,744	11/12/96	GAW ET AL				
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				FILING DATE July 10, 2001		GROUP 2815	
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO		
bwb 1	CCA	5-238894	09/17/93	JAPAN W/ENGLISH ABSTRACT			
	CCB	2 152 315	07/31/85	GREAT BRITAIN			
	CCC	2001-196892	07/19/01	JAPAN W/ENGLISH ABSTRACT			
	CCD	2000-278085	10/06/00	JAPAN (ENGLISH ABSTRACT)			
	CCE	WO 03/012874	02/13/03	WIPO			
	CCF	1 043 427	10/11/00	EUROPE			
	CCG	1 069 605	01/17/01	EUROPE			
	CCH	WO 02/099885	12/12/02	WIPO			
	CCI	10-269842	10/09/98	JAPAN W/ENGLISH ABSTRACT			
	CCJ	59066183	04/14/84	JAPAN (ENGLISH ABSTRACT)			
	CCK	03046384	02/27/91	JAPAN (ENGLISH ABSTRACT)			
	CCL	WO 02/11254	02/07/02	WIPO			
	CCM	0 494 514	07/15/92	EUROPE			
	CCN	0 247 722	12/02/87	EUROPE			
	CCO	1 037 272	09/20/00	EUROPE			
	CCP	59-073498	04/25/84	JAPAN (ENGLISH ABSTRACT)			
	CCQ	60-161635	08/23/85	JAPAN W/ENGLISH ABSTRACT			
CCR	59-044004	03/12/84	JAPAN W/ENGLISH ABSTRACT				
CCS	0 392 714	10/17/90	EUROPE				
	CCT						
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	CCV						
	CCW						
	CCX						
	CCY						
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OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)					
	LLAA	Peter Weiss; "Speed demon gets hooked on silicon"; Science News Online; Sept. 15, 2001; pp. 1-3			
	LLAB	"Motorola Develops New Super-Fast Chip"; USA Today; Sept. 4, 2001			
	LLAC	Lon Valigra; "Motorola Lays GaAs on Si Wafer"; AsiaBizTech; Nov. 2001pp. 1-3			
	LLAD	"Holy Grail! Motorola Claims High-Yield GaAs Breakthrough"; Micromagazine.com (no date available); pp. 1-3			
	LLAE	Jong-Gul YOON; "Growth of Ferroelectric LiNbO ₃ Thin Film on MgO-Buffered Si by the Sol-Gel Method"; Journal of the Korean Physical Society (Proc. Suppl.); Vol. 29, Nov. 1996; pp. S648-S651			
	LLAF	V. Bomand et al.; "Deposition of LiTaO ₃ thin films by pyrosol process"; Thin Solid Films 304 (1997); pp.239-244			
	LLAG	R. Droopad et al.; "Development of high dielectric constant epitaxial oxides on silicon by molecular beam epitaxy"; Materials Science and Engineering B87 (2001); pp.292-296			
	LLAH	A.K. Sharma et al.; "Integration of Pb(Zr _{0.52} Ti _{0.48})O ₃ epilayers with Si by domain epitaxy"; Applied Physics Letters, Vol. 76, No. 11; March 13, 2000; pp. 1458-1460			
	LLAI	Dwight C. Streit et al; "High Reliability GaAs-AlGaAs HBT's by MBE with Be Base Doping and InGaAs Emitter Contacts"; 8179 IEEE Electron Device Letters; 12(1991) September, No. 9, New York, US			
	LLAJ	C. Y. Hung et al; "Piezoelectrically induced stress tuning of electro-optic devices"; 320 Applied Physics Letters; 59(1991) 30 December, No. 27, New York, US			
	LLAK	J. Piprek; "Heat Flow Analysis of Long-Wavelength VCSELs with Various DBR Materials"; University of Delaware, Materials Science, Newark, DE, 19716-3106; Oct. 31, 1994; pp. 286-287			
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	LLAM	M.R. Wilson et al.; GaAs-On-Si: A GaAs IC Manufacturer's Perspective"; GaAs IC Symposium, IEEE, 1988; pp. 243-246			
	LLAN	Y. Kitano et al.; "Thin film crystal growth of BaZrO ₃ at low oxygen partial pressure"; Journal of Crystal Growth 243 (2002); pp. 164-169			
	LLAO	M.E. Hawley; et al; "Microstructural Study of Colossal Magneto-Resistive Films As a Function of Growth Temperature, As Deposited and Annealed"; 401, 1996; pp. 531-536			
LLAP					
LLAQ					
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